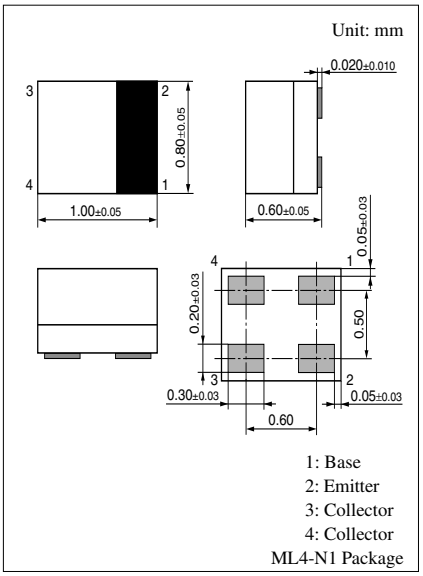
2SB1462L

Silicon PNP epitaxial planer type

For general amplification
Complementary to 2SD2216L



Marking Symbol: J

■ Features

- High foward current transfer ratio h_{FE}
- Mold leadless type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	−60	V
Collector to emitter voltage	V_{CEO}	−50	V
Emitter to base voltage	V_{EBO}	−7	V
Peak collector current	I_{CP}	−200	mA
Collector current	I_C	−100	mA
Collector power dissipation *	P_C	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

Note) *: Printed circuit board copper foil for collector portion area: 20.0 mm^2 or more, thickness: 1.6 mm

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -20$ V, $I_E = 0$			− 0.1	μA
	I_{CEO}	$V_{CE} = -10$ V, $I_B = 0$			−100	μA
Collector to base voltage	V_{CBO}	$I_C = -10$ μA, $I_E = 0$	−60			V
Collector to emitter voltage	V_{CEO}	$I_C = -100$ μA, $I_B = 0$	−50			V
Emitter to base voltage	V_{EBO}	$I_E = -10$ μA, $I_C = 0$	−7			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -10$ V, $I_C = -2$ mA	180		390	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100$ mA, $I_B = -10$ mA		− 0.3	− 0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		2.7		pF
Transition frequency	f_T	$V_{CB} = -10$ V, $I_E = 1$ mA, f = 200 MHz		80		MHz